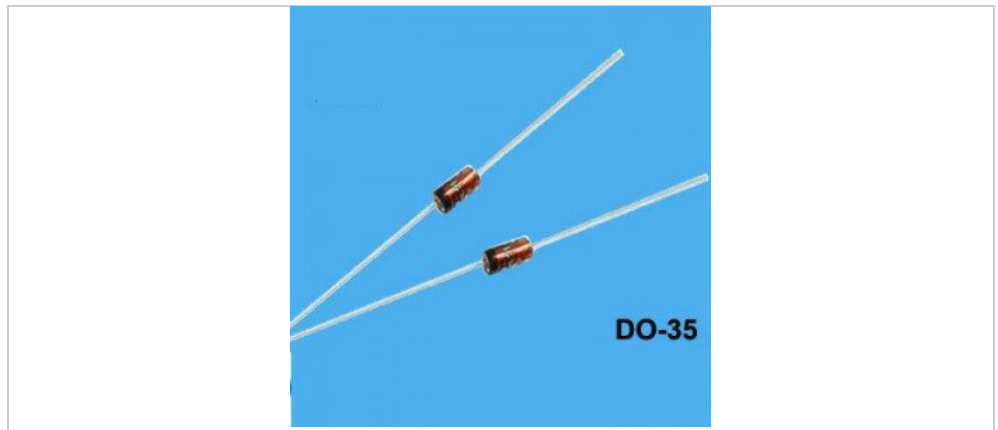




DB3 DB4 SILICON BIDIRECTIONAL DIACS DO-35



Specifications

DB3 DB4 SILICON BIDIRECTIONAL DIACS DO-35

Characteristics at T_a = 25 °C

Parameter		Symbol	Min.	Max.	Unit
Breakover Voltage	DB-3	V _{(BR)1} and V _{(BR)2}	28	36	V
	DB-4		35	45	
Breakover Currents		I _{(BR)1} and I _{(BR)2}	-	200	μA
Breakover Voltage Symmetry		[V _{(BR)1}]-[V _{(BR)2}]	-	3.8	V
Dynamic Breakover Voltage ΔI = [I _{BR} to I _F = 10 mA]		ΔV ±	5	-	V
Thermal Impedance Junction to Ambient Air		R _{θJA}	-	60	°C/W